SiRA99DP -30 V P-CHANNEL MOSFET

THE LOWEST $R_{DS(on)}$ AND R_{DS} - Q_g FOM IN ITS CLASS

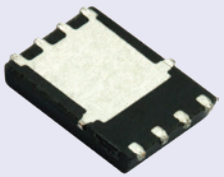
BEST IN CLASS $R_{DS(on)}$

- Typical $R_{DS(on)}$ = 1.3 mΩ
- Maximum $R_{DS(on)}$ = 1.7 mΩ
- Minimizes I^2R voltage drop across power path
- Reduces conduction loss

REDUCE COMPONENT COUNT TO SIMPLIFY DESIGNS

- Compared to n-channel devices, eliminates the need for a drive circuit and charge pump
- Achieves high efficiency with less components
- Enables higher power density

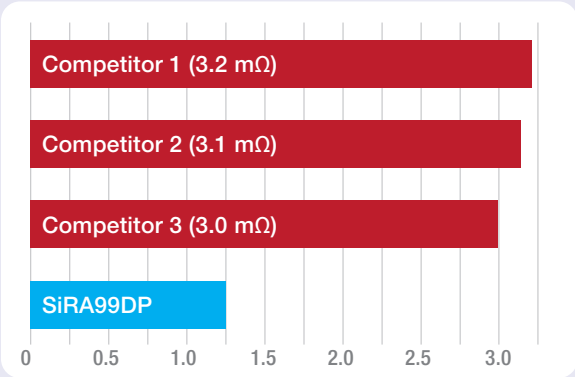
INDUSTRY-LEADING $R_{DS(on)}$ FOR HIGHER POWER DENSITY



PowerPAK® SO-8
SiRA99DP

SIMPLIFIES DRIVE CIRCUITS

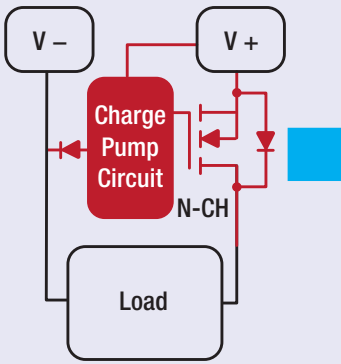
TYPICAL $R_{DS(on)}$ (mΩ) AT V_{GS} = 10 V



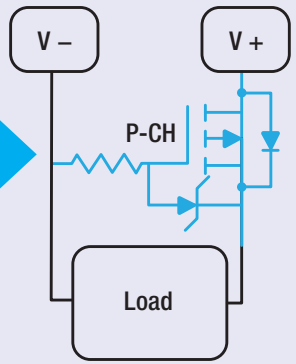
EXCELLENT R_{DS} - Q_g FOM OPTIMIZED FOR SWITCHING

- Features best in class R_{DS} - Q_g FOM
- Very low Q_{gd}, with short Miller plateau
- Q_{gd} /Q_{gs} ratio < 1
- Reduces conduction loss

OR-ING SOLUTION WITH N-CHANNEL MOSFET



OR-ING SOLUTION WITH P-CHANNEL MOSFET



APPLICATIONS

- Power adapter switch and load switch
- OR-ing
- Battery and circuit protection
- Motor drive control

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